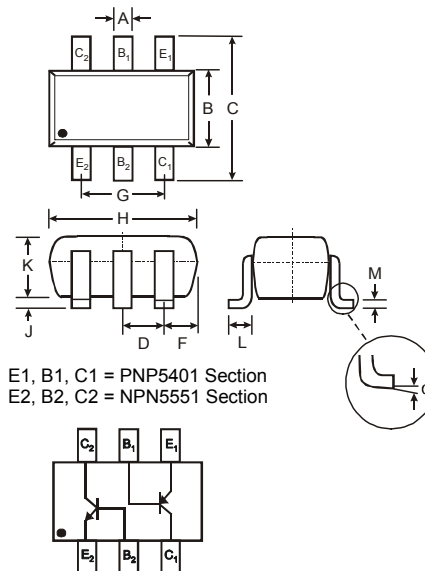


Features

- Complementary Pair One 5551-Type NPN
One 5401-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 4 and 5)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: KNM, See Page 5
- Ordering & Date Code Information: See Page 5
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings, NPN 5551 Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	NPN5551	Unit
Collector-Base Voltage	V_{CB0}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	200	mA
Power Dissipation (Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Maximum Ratings, PNP 5401 Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	PNP5401	Unit
Collector-Base Voltage	V_{CB0}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current – Continuous (Note 1)	I_C	-200	mA
Power Dissipation (Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Maximum combined dissipation.
 3. No purposefully added lead.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 5. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics, NPN 5551 Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	50	nA μA	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
Emitter Cutoff Current	I_{EBO}	—	50	nA	$V_{EB} = 4.0\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	80 80 30	— 250 —	—	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.15 0.20	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.0	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Small Signal Current Gain	h_{fe}	50	250	—	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	f_T	100	300	MHz	$V_{CE} = 10\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	8.0	dB	$V_{CE} = 5.0\text{V}, I_C = 200\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

Electrical Characteristics, PNP 5401 Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-160	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-150	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	-50	nA μA	$V_{CB} = -120\text{V}, I_E = 0$ $V_{CB} = -120\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
Emitter Cutoff Current	I_{EBO}	—	-50	nA	$V_{EB} = -3.0\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	50 60 50	— 240 —	—	$I_C = -1.0\text{mA}, V_{CE} = -5.0\text{V}$ $I_C = -10\text{mA}, V_{CE} = -5.0\text{V}$ $I_C = -50\text{mA}, V_{CE} = -5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.2 -0.5	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-1.0	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Small Signal Current Gain	h_{fe}	40	200	—	$V_{CE} = -10\text{V}, I_C = -1.0\text{mA}, f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	f_T	100	300	MHz	$V_{CE} = -10\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	8.0	dB	$V_{CE} = -5.0\text{V}, I_C = -200\mu\text{A}, R_S = 10\Omega, f = 1.0\text{kHz}$

Notes: 6. Short duration pulse test used to minimize self-heating effect.

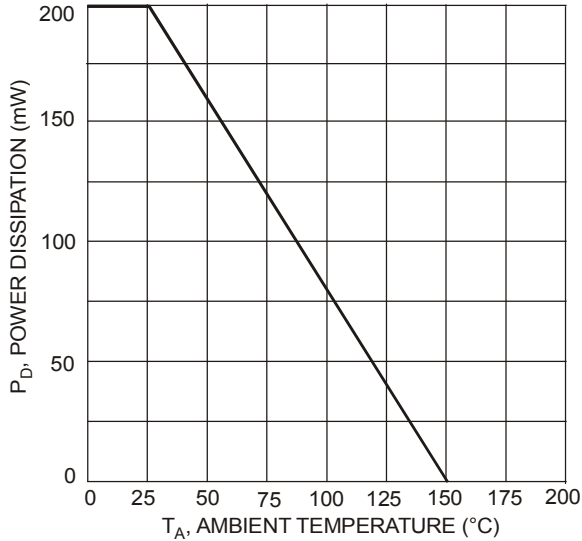


Fig. 1, Max Power Dissipation vs. Ambient Temperature (Total Device)

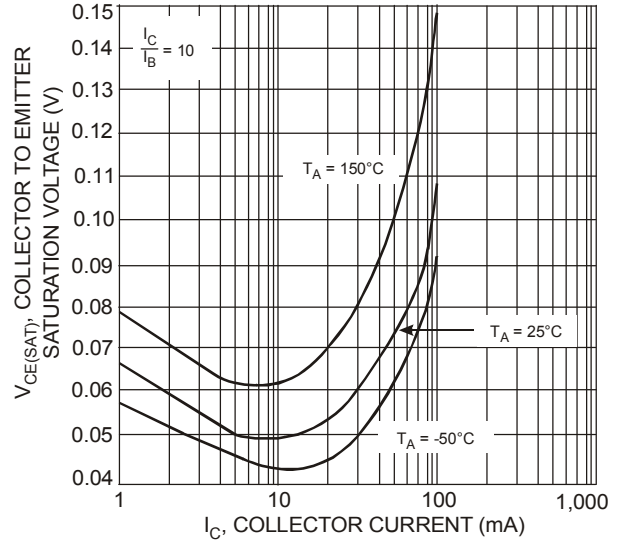


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current (NPN5551)

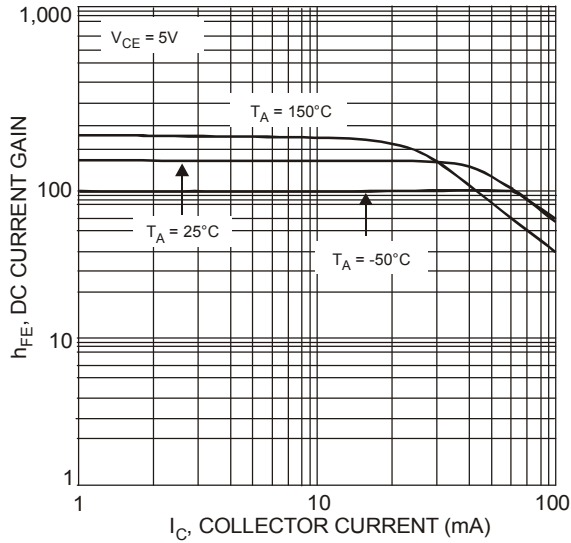


Fig. 3, DC Current Gain vs. Collector Current (NPN5551)

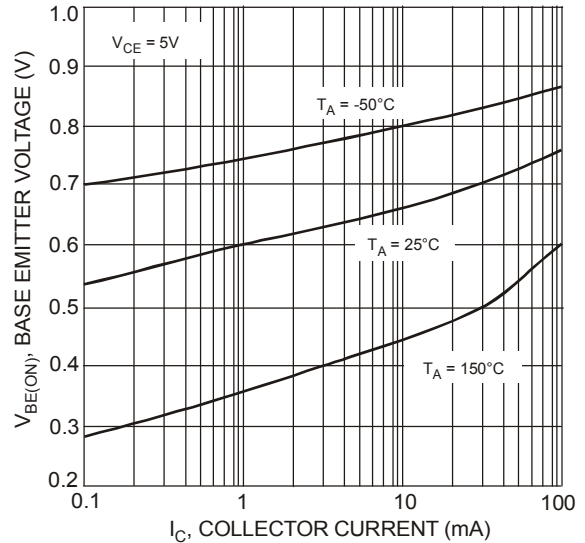


Fig. 4, Base Emitter Voltage vs. Collector Current (NPN5551)

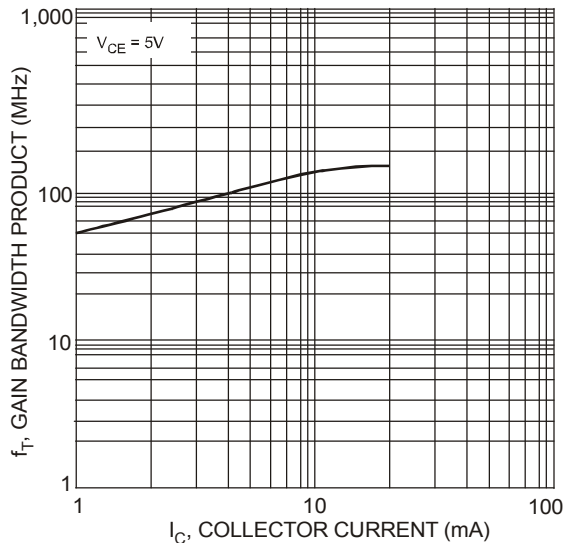


Fig. 5, Gain Bandwidth Product vs. Collector Current (NPN5551)

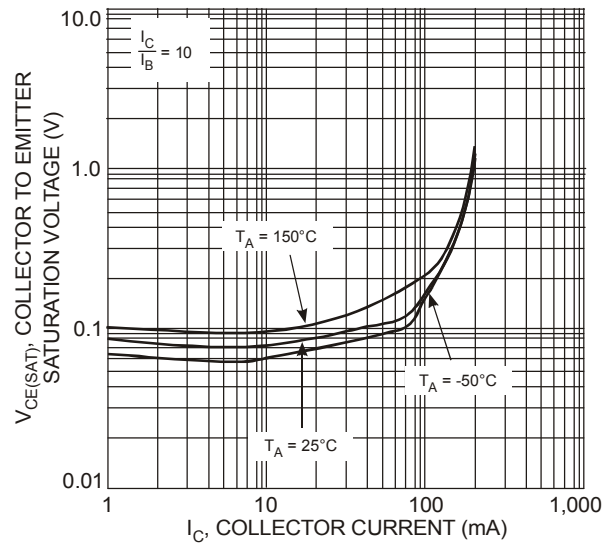


Fig. 6, Collector Emitter Saturation Voltage vs. Collector Current (PNP5401)

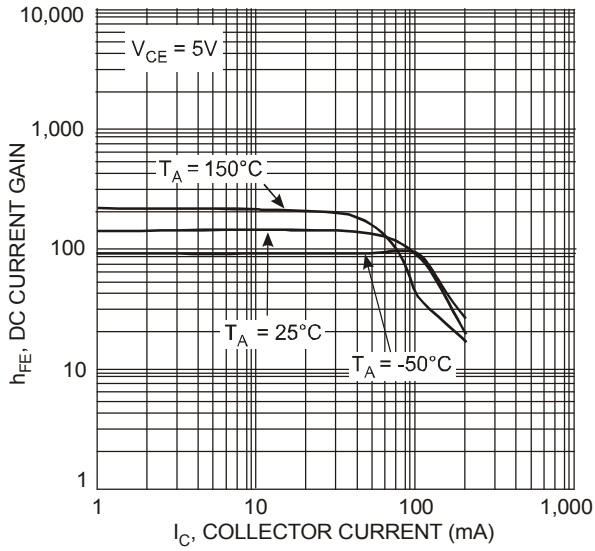


Fig. 7, DC Current Gain vs. Collector Current (PNP5401)

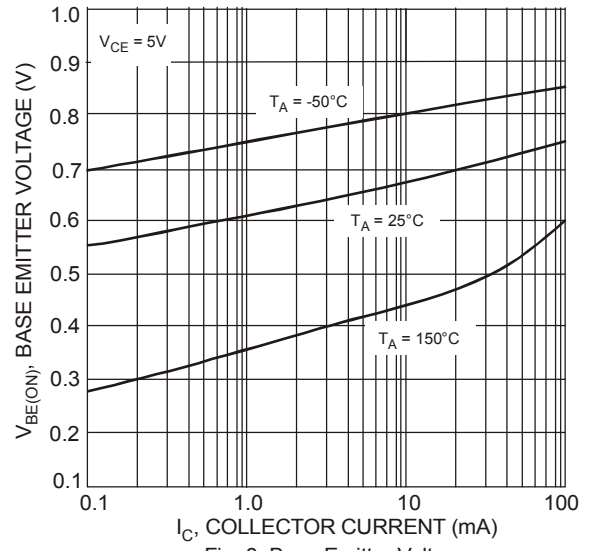


Fig. 8, Base Emitter Voltage vs. Collector Current (PNP5401)

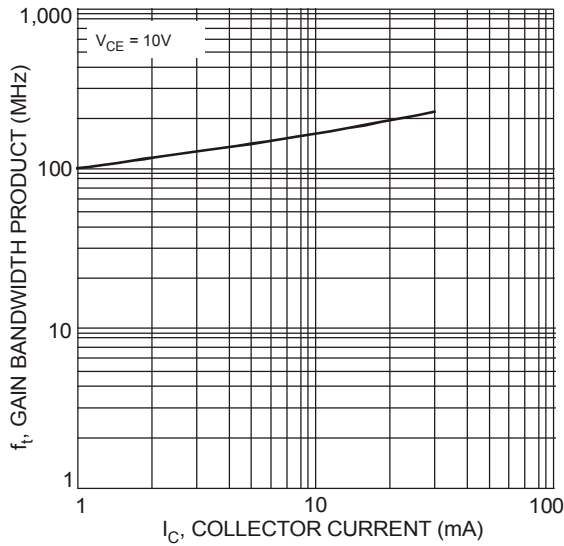


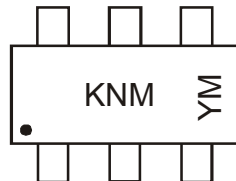
Fig. 9, Gain Bandwidth Product vs. Collector Current (PNP5401)

Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT5451-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



KNM = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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